

Patent  
Attorney's Docket No. 033022-004

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Yukio SHAKUDA

Application No.: 09/604,097

Filed: June 27, 2000

For: SEMICONDUCTOR LIGHT EMITTING  
DEVICE AND MANUFACTURING  
METHOD THEREFOR

Group Art Unit: 2874

Examiner: Unassigned

INFORMATION DISCLOSURE STATEMENT  
TRANSMITTAL LETTERAssistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Enclosed is an Information Disclosure Statement and accompanying form PTO-1449 for the above-identified patent application.

- ☒ No additional fee for submission of an IDS is required.
- ☐ The fee of \$180.00 (126) as set forth in 37 C.F.R. § 1.17(p) is also enclosed.
- ☐ A certification under 37 C.F.R. § 1.97(e) is also enclosed.
- ☐ A certification under 37 C.F.R. § 1.97(e), and the fee of \$180.00 (126) as set forth in 37 C.F.R. § 1.17(p) are also enclosed.
- ☐ Charge \$\_\_\_\_\_ to Deposit Account No. 02-4800 for the fee due.
- ☐ A check in the amount of \$\_\_\_\_\_ is enclosed for the fee due.

The Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17 and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 02-4800. This paper is submitted in duplicate.

Respectfully submitted,

BURNS, DOANE, SWECKER &amp; MATHIS, L.L.P.

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Date: March 6, 2002

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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents  
 Washington, D.C. 20231

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. § 1.56, Applicant hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed.

The documents are being submitted within 3 months of the filing or entry of the national stage of this application or before the first Office Action on the merits, whichever is later, therefore no fee or statement is required under 37 C.F.R. § 1.97(b).

To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initialed copy of this form be returned to the undersigned.

Adjustment dates 02/14/2003 EFM/NAV  
 06/12/2002 JAT/TIS 00000001 024000 05604027  
 01 FC:126 180.00 CR

Respectfully submitted,

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(01/02)

SHEET 1 OF 3

Substitute for form 1449A/PTO	ATTORNEY'S DKT NO.	APPLICATION NO.
	033022-004	09/604,097
	APPLICANT	
	Yukio Shakuda	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	FILING DATE	GROUP
	June 27, 2000	2874

U.S. PATENT DOCUMENTS				
Examiner Initials	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication (MM-DD-YYYY)
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Examiner Initials	Foreign Patent Document		Country	Date of Publication (MM-DD-YYYY)	Translation	
	Number	Kind Code (if known)			Yes	no
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	0 541 373 B1		Europe	09/30/1998		
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Examiner Initials	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
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Examiner Signature	Date Considered

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

(05/01)

SHEET 2 OF 3

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NON-PATENT LITERATURE DOCUMENTS						
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